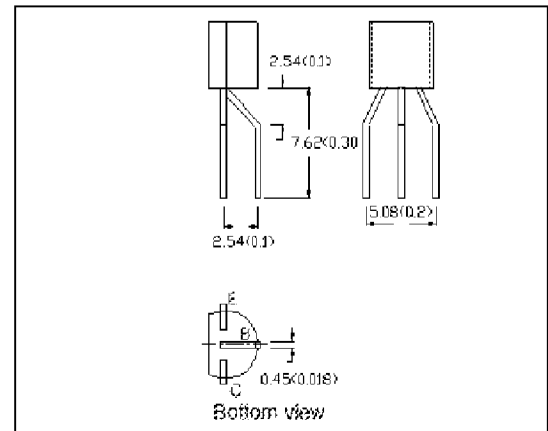


DESCRIPTION

CL117 is NPN silicon planar transistor designed for general purpose high voltage and video amplifier application.

TO-92F (LEAD FORM to MELF-002)



ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	120V
Collector-Base Voltage	V _{CB0}	120V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current Continuous	I _C	100mA
Total Power Dissipation @ Ta < 25°C	P _{tot}	625mW
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(Ta = 25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS	
Collector-Emitter Breakdown Voltage	LV _{CEO} *	120		V	I _C = 30mA	I _B = 0
Collector-Base Breakdown Voltage	BV _{CB0}	120		V	I _C = 0.1mA	I _E = 0
Emitter-Base Breakdown Voltage	BV _{EB0}	5		V	I _E = 0.01mA	I _C = 0
Collector Cutoff Current	I _{CB0}		100	nA	V _{CB} = 75V	I _E = 0
Emitter Cutoff Voltage	I _{EB0}		100	nA	V _{EB} = 4V	I _C = 0
D.C. Current Gain	H _{FE} *	25			I _C = 10mA	V _{CE} = 10V
		30			I _C = 30mA	V _{CE} = 10V
Collector-Emitter Saturation Voltage	V _{CE(sat)} *		0.2	V	I _C = 50mA	I _B = 5mA
Base-Emitter Saturation Voltage	V _{BE(sat)} *		0.9	V	I _C = 50mA	I _B = 5mA
Current Gain Bandwidth Product	f _T	40		MHz	I _C = 30mA	V _{CE} = 10V
Output Capacitance	C _{ob}	6	TYP.	pF	f = 20MHz	
					V _{CB} = 10V	f = 1MHz

* Pulse test : pulse width < 300μs, duty cycle < 1%.



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